

09/636,484

APPLICANT

LIST OF REFERENCES CITED BY APPLICANT

FILING DATE

GROUP

08-10-2000

2811

## U.S. PATENT DOCUMENTS

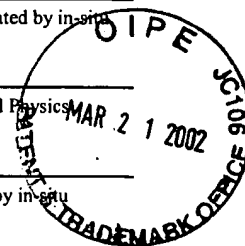
EXAMINER INITIAL		DOCUMENT NUMBER	DATE (Issue)	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
DN	AA	4,416,952	12-1983	Nishizawa	428	698	
DN	AB	4,561,915	12-1985	Mito	148	171	
DN	AC	4,745,082	5-1998	Kwok	437	39	
DN	AD	4,802,180	1-1989	Brandle Jr. et. al.	372	41	
DN	AE	4,843,450	6-1989	Kirchner et. al.	257	38	
DN	AF	4,859,253	8-1989	Buchanan et. al.	148	33	
DN	AG	4,935,789	6-1990	Calviello	357	22	
DN	AH	5,124,762	6-1992	Childs et. al.	357	16	
DN	AI	5,451,548	9-1995	Hunt et. al.	437	225	
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DN	AL	5,665,658	9-1997	Passlack	438	763	
DN	AM	5,693,565	12-1997	Camilletti et. al.	357	22	
DN	AN	5,767,388	6-1998	Fleischer et. al.	73	31	
DN	AO	5,821,171	10-1998	Hong et. al.	438	767	
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DN	AR	6,006,582	12-1999	Bhandari et. al.	73	232	
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DN	AU	6,094,295	7-2000	Passlack et. al.	359	321	
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DN	AW	6,207,976	3-2001	Takahashi et. al.	257	192	
DN	AX	6,313,511	11-2001	Noguchi	257	392	
	AY						
	AZ						

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		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
DN	BA	JP 8085873 A	4-1998	JAPAN, Yoshizawa et. al.	yes	
	BB					
	BC					
	BD					
	BE					
	BF					
	BG					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

DHL	BH	Passlack et. al., "Thermodynamic and photochemical stability of low interface state density Ga <sub>2</sub> O <sub>3</sub> -GaAs structures fabricated by in-situ molecular beam epitaxy", Applied Physics Letters, Volume 69, Number 3, pages 302-304, 15 July 1996
DHL	BI	Passlack et. al., " Recombination velocity at oxide-GaAs interfaces fabricated by in-situ molecular beam epitaxy", Applied Physics Letters, Volume 68, Number 25, pages 3605-3607, 17 June 1997
DHL	BJ	Passlack et. al. "Quasistatic and high frequency capacitance-vltage characterization of Ga <sub>2</sub> O <sub>3</sub> -GaAs structures fabricated by in-situ molecular beam epitaxy", Applied Physics Letters, Volume 68, Number 8, pages 1099-1101, 19 February 1996
bhl	BK	Ueda et. al. "Anisotropy of electrical and optical properties in B-Ga <sub>2</sub> O <sub>3</sub> single crystals", Applied Physics Letters, Volume 71, Number 7, Pages 933-935, 18 August 1997
DHL	BL	Ueda et. al. "Synthesis and control of conductivity of ultraviolet transmitting B-Ga <sub>2</sub> O <sub>3</sub> single crystals", Applied Physics Letters, Volume 70, Number 26, pages 3561-3563, 30 June 1997



Examiner Donghee Kang Date Considered 6-28-02

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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